

THYRISTOR MODULE

PK(PD,PE)130FG

TOP



UL:E76102 (M)

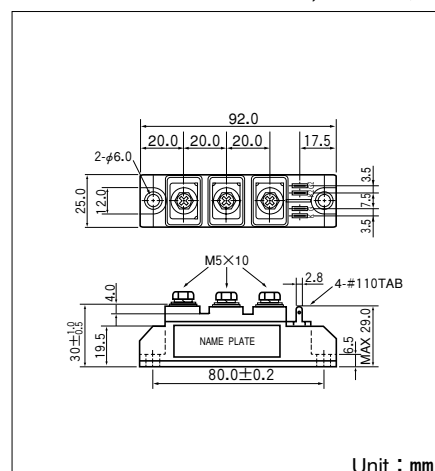
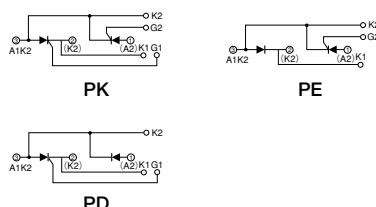
Power Thyristor/Diode Module **PK130FG** series are designed for various rectifier circuits and power controls. For your circuit application, following internal connections and wide voltage ratings up to 1600V are available. and electrically isolated mounting base make your mechanical design easy.

- $I_{T(AV)}$ 130A, $I_{T(RMS)}$ 205A, I_{TSM} 3500A
- di/dt 100A/ μs
- dv/dt 1000V/ μs

(Applications)

Various rectifiers
AC/DC motor drives
Heater controls
Light dimmers
Static switches

Internal Configurations



Unit : mm

Maximum Ratings

($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Item	Ratings				Unit
		PK130FG40	PK130FG80	PK130FG120	PK130FG160	
V_{RRM}	* Repetitive Peak Reverse Voltage	400	800	1200	1600	V
V_{RSM}	* Non-Repetitive Peak Reverse Voltage	480	960	1300	1700	V
V_{DRM}	* Repetitive Peak off-state Voltage	400	800	1200	1600	V

Symbol	Item		Conditions	Ratings	Unit
IT(AV)	* Average On-state Current		Single phase, half wave, 180° conduction, Tc=83℃	130	A
IT(RMS)	* R.M.S. On-state Current		Single phase, half wave, 180° conduction, Tc=83℃	205	A
ITSM	* Surge On-state Current		1/2 Cycle, 50/60Hz, Peak Value, non-repetitive	3200/3500	A
I²t	* I²t		Value for one cycle surge current	51040	A²S
PGM	Peak Gate Power Dissipation			10	W
PG(AV)	Average Gate Power Dissipation			1	W
IFGM	Peak Gate Current			3	A
VFGM	Peak Gate Voltage (Forward)			10	V
VRGM	Peak Gate Voltage (Reverse)			5	V
di/dt	Critical Rate of Rise of On-state Current		IG=100mA, VD=1/2VDRM, diG/dt=0.1A/μs	100	A/μs
Viso	* Isolation Breakdown Voltage (R.M.S.)		A.C. 1minute	2500	V
Tj	* Operating Junction Temperature			−40 to +125	℃
Tstg	* Storage Temperature			−40 to +125	℃
	Mounting Torque	Mounting (M5)	Recommended Value 1.5-2.5 (15-25)	2.7 (28)	N·m (kgf·cm)
		Terminal (M5)	Recommended Value 1.5-2.5 (15- 25)	2.7 (28)	
	Mass		Typical Value	170	g

Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
I_{DRM}	Repetitive Peak off-state Current,max	$T_j=125^\circ\text{C}$, $V_D=V_{DRM}$	35	mA
I_{RRM}	* Repetitive Peak Reverse Current,max	$T_j=125^\circ\text{C}$, $V_D=V_{DRM}$	35	mA
V_{TM}	* Gn-state Voltage,max	$I_T=390\text{A}$	1.6	V
I_{GT}	Gate Trigger Current,max	$V_D=6\text{V}$, $I_T=1\text{A}$	50	mA
V_{GT}	Gate Trigger Voltage,max	$V_D=6\text{V}$, $I_T=1\text{A}$	3	V
V_{GD}	Gate Non-Trigger Voltage,min	$T_j=125^\circ\text{C}$, $V_D=\frac{1}{2}V_{DRM}$	0.25	V
dv/dt	Critical Rate of Rise of off-state Voltage,min	$T_j=125^\circ\text{C}$, $V_D=\frac{2}{3}V_{DRM}$	1000	V/ μs
$R_{th(j-c)}$	* Thermal Impedance,max	Junction to case	0.2	$^\circ\text{C}/\text{W}$

* mark : Thyristor and Diode part. No mark : Thyristor part

